Task ID: 425.030

<u>Task Title:</u> Supercritical Carbon Dioxide Compatible Additives: Design, Synthesis, and Application of an Environmentally Friendly Development Process to Next Generation Lithography: Resists and Additives

<u>Deliverable:</u> Report on new development additives including silazanes

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Abstract:

Supercritical carbon dioxide ($scCO_2$) is considered as an environmentally benign replacement for organic solvents in many microelectronic applications. Its unique properties are also beneficial for it to be used as a developing solvent for photoresists patterning. However, most conventional photoresists are generally not soluble in $scCO_2$. Previously, we have reported the use of fluorinated quaternary ammonium salts to assist in the dissolution of photoresists in $scCO_2$. In order to make the process more environmentally benign, it is desirable to eliminate fluorine. In this report, we present several non-fluorinated additives to develop photoresists in $scCO_2$ and the proposed dissolution mechanism.

Introduction:

Carbon dioxide is nontoxic, nonflammable, inert under most conditions and has been used as an environmentally benign replacement for organic solvents in many microelectronic applications [1]. Supercritical carbon dioxide ($scCO_2$) exhibits the unique properties as combining liquid-like densities with gas-like diffusivities and zero surface tension. Therefore, it could be utilized as a developer for photoresist processing. However, conventional photoresists are generally not soluble in $scCO_2$, which limits its practical use. For pure $scCO_2$ processing, certain fluorinated or silicon containing polymers have been used. Ober et al. have showed the ability to develop fluorinated photoresists in $scCO_2$ [2,3]. It is believed that the presence of fluorine increases the solubility of polymers in $scCO_2$, but high content of fluorine has an adverse effect on the etch resistance. Therefore, conventional photoresists generally are not fluorinated and require additives such as cosolvents to be developed in $scCO_2$ [4].

In the previous report, we have shown the development of two conventional photoresists, poly(4-t-butoxycarbonyloxystyrene) (PBOCST) and poly(hydroxystyrene-co-t-butylacrylate)(PHS-co-PS-co-PtBA)(ESCAP) in scCO₂ with quaternary ammonium salts(QAS). However, it is desirable to make the process more environmentally friendly by eliminating the use of fluorinated compounds. Therefore, many non-fluorinated additives have been considered and tested for developing photoresists in scCO₂.

Experimental:

(N,N-Dimethyl)trimethyl silane 1-(trimethylsilyl)imidazole N,O-Bis-(trimethylsilyl)-acetamide

Figure 1 Chemical structures of new development additives

Lithographic Evaluation. Each resist film was spin-coated on an HMDS-primed silicon wafer and baked at 130°C for 60 seconds. Dose testing was performed by using a GCA Autostep 200 DSW i-line Wafer Stepper (500mW/cm²). After exposure, ESCAP and PBOCST were baked at 115°C and 90°C for 60 seconds, respectively.

Development in Supercritical CO₂. The chemical structures of new development additives are shown in Figure 1. Each additive was dissolved in scCO₂ at 50°C and 5000 psi for 10-15 minutes and was subsequently used to develop each resist film for 5-15 minutes by using a scCO₂ dissolution rate monitor described elsewhere [6].

Metrology. A Tencor P10 profilometer was used to measure the film thickness of each photoresist before and after development. The developed patterns were examed using the Nikon Digital Sight D5-5M-L1 optical microscope and the LEO 1550 FESEM scanning electron microscope.

Results and Discussion:

The additives are able to react with the hydroxy groups in each photoresist and increase their solubility in $scCO_2$. As shown in Figure 2, the hydroxy groups in unexposed ESCAP could react with (N,N-dimethyl)trimethyl silane(DMTS) and form trimethylsilyl (TMS) groups to increase the solubility of the resist in $scCO_2$.

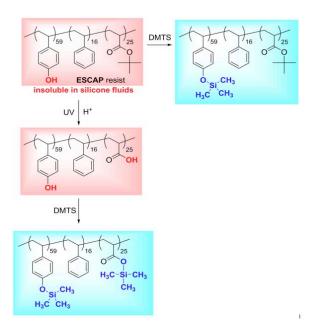


Figure 2 Reaction of ESCAP with DMTS

It was found that ESCAP wasn't completely silylated by only using DMTS. Therefore, saccharin or 1-(trimethylsilyl)imidazole(TMSI) were mixed with DMTS as catalysts to increase the amount of silylation. The result of ESCAP developed in $scCO_2$ using DMTS and saccharin is shown in Figure 3. As the unexposed ESCAP dissolved in $scCO_2$, a negative-tone image was developed.

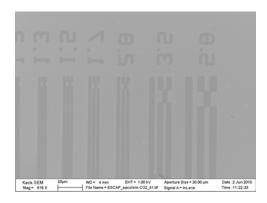


Figure 3 ESCAP developed in scCO₂ using DMTS

N,O-Bis-(trimethylsilyl)-acetamide (BSA) is a stronger silylating reagent compared to DMTS and does not require any catalyst to develop ESCAP in $scCO_2$. However, both exposed and unexposed ESCAP dissolved in $scCO_2$ with the aid of BSA and therefore requires more optimization.

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